

SMALL SIGNAL PNP TRANSISTORS

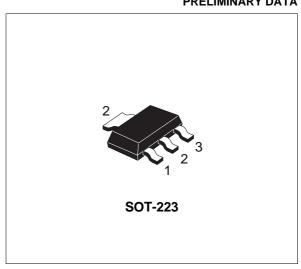
PRELIMINARY DATA

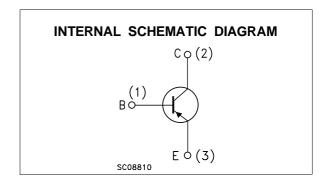
Ordering Code	Marking
BSP31	P31
BSP33	P33

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTORS
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPES ARE BSP41 AND BSP43 RESPECTIVELY

APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BSP31	BSP33	
V _{CBO}	Collector-Base Voltage (I _E = 0)	-70	-90	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	-60	-80	V
V _В	Emitter-Base Voltage (Ic = 0)	-	5	V
Ic	Collector Current	-	1	Α
I _{CM}	Collector Peak Current (tp < 5 ms)	-	2	Α
I_{B}	Base Current	-0).1	Α
I _{BM}	Base Peak Current (tp < 5 ms)	-0).2	Α
P_{tot}	Total Dissipation at T _{amb} = 25 °C	1.3		W
T _{stg}	Storage Temperature	-65 to 150		°C
Tj	Max. Operating Junction Temperature	1:	50	°C

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THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	96.1	°C/W	
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Device mounted on a PCB area of 1 cm²

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

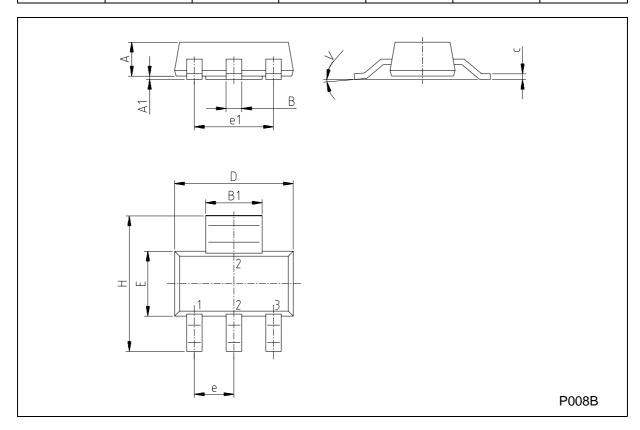
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _E = 0)	V _{CB} = -60 V V _{CB} = -60 V	T _j = 150 °C			-100 -50	nΑ μΑ
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = -5 V				-100	nA
V _(BR) CBO	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA for BSP31 for BSP33		-70 -90			V V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -20 mA for BSP31 for BSP33		-60 -80			V V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA		-5			V
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	I _C = -150 mA I _B : I _C = -500 mA I _B :				-0.25 -0.5	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = -150 mA I _B : I _C = -500 mA I _B :				-1 -1.2	V V
h _{FE} *	DC Current Gain	$I_C = -100 \mu\text{A}$ V_C $I_C = -100 \text{mA}$ V_C $I_C = -500 \text{mA}$ V_C	_	30 100 50		300	
f⊤	Transition Frequency	f = 100 MHz	E = -10 V	100			MHz

^{*} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 1.5 %

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SOT-223 MECHANICAL DATA

DIM.	mm			inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			1.80			0.071	
В	0.60	0.70	0.80	0.024	0.027	0.031	
B1	2.90	3.00	3.10	0.114	0.118	0.122	
С	0.24	0.26	0.32	0.009	0.010	0.013	
D	6.30	6.50	6.70	0.248	0.256	0.264	
е		2.30			0.090		
e1		4.60			0.181		
E	3.30	3.50	3.70	0.130	0.138	0.146	
Н	6.70	7.00	7.30	0.264	0.276	0.287	
V			10°			10°	
A1		0.02					



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